CLAIM AMENDMENTS

1. (Currently Amended) A high power semiconductor device ~~having~~ comprising:

a plurality of gate electrodes~~, the device comprising:~~;

an active region ~~of~~ having an approximately rectangular shape ~~formed~~, located on a semiconductor substrate;

a drain electrode ~~formed~~ located on the active region; and

~~a~~ first and ~~a~~ second source electrodes disposed on the ~~both~~ opposite sides ~~to~~ of the drain electrode ~~in such a manner~~ so that the first and the second source electrodes face each other across at least some of the gate electrodes, wherein ~~the directions of~~ currents carried by the first and the second source electrodes ~~are~~ flow in opposite ~~to~~ directions from each other.

2. (Currently Amended) The semiconductor device according to claim 1, ~~wherein~~ including a first source via hole connected ~~with~~ to the first source electrode and a second source via hole connected ~~with~~ to the second source electrode ~~are~~, respectively disposed in regions which face each other across the active region.

3. (Currently Amended) The semiconductor device according to claim 2, ~~wherein all of the~~ including source wires connected ~~with~~ to the first and ~~the~~ second source via holes ~~are~~, all of the source wires being connected ~~with~~ to the source via holes by air bridges which extend along ~~the~~ a width direction of ~~the width of~~ electrodes ~~of~~ connected to the source wires.

4. (Currently Amended) The semiconductor device according to claim 2, wherein the first source via hole is ~~arranged off~~ offset from a position which faces the second source via hole across the active region.

5. (Currently Amended) The semiconductor device according to claim 2, comprising a gate pad disposed adjacent to the first source via hole and a drain pad disposed adjacent to the second source via hole, wherein the source electrodes which are connected ~~with~~ to the first source via hole outnumber the source electrodes which are connected ~~with~~ to the second source via hole.

6. (Currently Amended) The semiconductor device according to claim 1, comprising a plurality of gate wires to which any one of the plurality of gate electrodes is connected, wherein the gate wires are connected ~~with~~ to a grounded capacitance via a resistor.

7. (Currently Amended) The semiconductor device according to claim 6, comprising an external connection pad which is connected ~~with~~ to the resistor, wherein the external connection pad and the capacitance are connected by a wire.

8. (Currently Amended) A high power semiconductor device ~~having~~ comprising:

a plurality of source electrodes~~, the device comprising:~~;

an active region ~~of~~ having an approximately rectangular shape ~~formed~~, located on a semiconductor substrate;

a plurality of source electrodes ~~formed~~ located on the active region;

a drain electrode disposed such that the drain electrode faces the source electrodes across ~~a~~ one of the gate ~~electrode~~ electrodes; and

a bridge wire disposed above the source electrodes and connecting the source electrodes ~~with~~ to each other, wherein the source electrodes are connected with each other by the bridge wire so that ~~the directions of~~ currents carried by the source electrodes ~~are~~ flow in directions alternately opposite to each other.

9. (Currently Amended) The semiconductor device according to claim 8, wherein the bridge wire ~~is formed by a~~ includes first and ~~a~~ second bridge wires, and the source electrodes connected with the first bridge wire and the source electrodes connected with the second bridge wire are disposed alternately.

10. (Currently Amended) The semiconductor device according to claim 8, wherein the bridge wire ~~is formed by~~ includes a plurality of bridge wires connecting ~~between~~ the source electrodes which are adjacent to each other ~~in such a manner~~ so that the plurality of source electrodes are connected in series.

11. (Currently Amended) The semiconductor device according to claim 8, comprising a plurality of gate wires to which any one of the plurality of gate electrodes is connected, wherein the gate wires are connected ~~with~~ to a grounded capacitance via a resistor.

12. (Currently Amended) The semiconductor device according to claim 11, comprising an external connection pad which is connected ~~with~~ to the resistor, wherein the external connection pad and the capacitance are connected by a wire.